

Page 4, please amend the paragraph beginning with "In addition" to read as follows:

In addition, if the flow rate ratio of C_4F_8 and N_2 (N_2 flow rate / C_4F_8 flow rate) in the processing gas is less than 10, an etching stop occurs and, as a result, deep etching is not achieved. Accordingly, it is desirable to set the flow rate ratio of C_4F_8 and N_2 in the processing gas essentially within a range of $10 \leq (N_2 \text{ flow rate} / C_4F_8 \text{ flow rate})$.

IN THE CLAIMS:

Please cancel claims 6 and 12 without prejudice or disclaimer of the subject matter thereof; amend claims 1 and 7; and add new claims 13-16, as follows:

1. (Amended) An etching method for etching an etching target film formed on a substrate placed inside an airtight processing chamber by inducing a processing gas

into said processing chamber, wherein;

said processing gas contains at least a C_xF_y gas and N_2 , but does not contain O_2 ;

and

~~said etching target film is constituted of an upper organic film containing Si and a~~
lower SiO_2 film.

7. (Amended) An etching method for etching an etching target film formed on a substrate placed inside an airtight processing chamber by inducing a processing gas into said processing chamber, wherein;

said processing gas contains at least a C_xF_y gas and N_2 , but does not contain O_2 ;

and

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said etching target film is constituted of an upper organic film containing Si and a lower SiN film.

-- 13. (New) An etching method according to claim 1, wherein;

said C_xF_y gas is CF_4 .

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14. (New) An etching method according to claim 13, wherein;

the flow rate ratio of CF_4 and N_2 in said processing gas is essentially set within a range of $1 \leq (N_2 \text{ flow rate} / CF_4 \text{ flow rate}) \leq 4$.

15. (New) An etching method according to claim 7, wherein;

said C_xF_y gas is C_4F_8 .

16. (New) An etching method according to claim 15, wherein;

the flow rate ratio of C_4F_8 and N_2 in said processing gas is essentially set within a range of $10 \leq (N_2 \text{ flow rate} / C_4F_8 \text{ flow rate})$. --

IN THE DRAWINGS:

Submitted herewith is a Request for Approval of Drawing Change. Subject to the approval of the Examiner, Applicants propose to replace " N_2 ," " H_2 ," and " CF_4 " in Fig. 1